

FDC6432SH

12V P-Channel PowerTrench® MOSFET, 30V PowerTrench® SyncFET

General Description

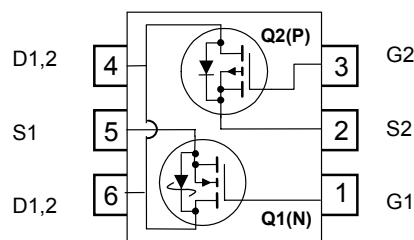
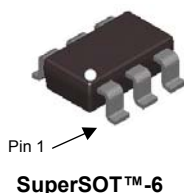
This complementary P-Channel MOSFET with SyncFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for providing an extremely low $R_{DS(ON)}$ in a small package.

Applications

DC/DC converter
Power management

Features

- SyncFET $R_{DS(ON)} = 90\text{ m}\Omega @ V_{GS} = 10\text{ V}$
2.4 A, 30V $R_{DS(ON)} = 105\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- P channel $R_{DS(ON)} = 90\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
-2.5 A, -12V $R_{DS(ON)} = 125\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$
 $R_{DS(ON)} = 220\text{ m}\Omega @ V_{GS} = -1.8\text{ V}$
- Fast switching speed.
- High performance trench technology for extremely low $R_{DS(ON)}$



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings		Units
		Q1 (N)	Q2 (P)	
V_{DSS}	Drain-Source Voltage	30	-12	V
V_{GSS}	Gate-Source Voltage	± 16	± 8	V
I_D	Drain Current— Continuous (Note 1a) — Pulsed	2.4	-2.5	A
		7	-7	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b)	1.3		W
		0.7		
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a) (Note 1b)	100	$^\circ\text{C/W}$
		175	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	60	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.432	FDC6432SH	7"	8mm	3000 units

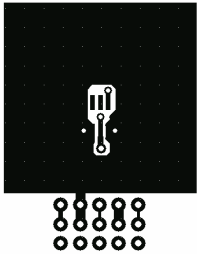
Electrical Characteristics <small>T_A = 25°C unless otherwise noted</small>							
Symbol	Parameter	Test Conditions	Q	Min	Typ	Max	Units
Off Characteristics							
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA V _{GS} = 0 V, I _D = -250 μA	Q1 Q2	30 -12			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Ref to 25°C I _D = -250 μA, Ref to 25°C	Q1 Q2		25 -10		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V V _{DS} = -10 V, V _{GS} = 0 V	Q1 Q2			500 1	μA
I _{GSS}	Gate-Body Leakage	V _{GS} = ±16 V, V _{DS} = 0 V V _{GS} = ±8 V, V _{DS} = 0 V	Q1 Q2			±100 ±100	nA
On Characteristics							
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 1 mA V _{DS} = V _{GS} , I _D = -250 μA	Q1 Q2	1 -0.4	1.5 -0.7	3 -1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 1 mA, Ref to 25°C I _D = -250 μA, Ref to 25°C	Q1 Q2		-7 3		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 2.4A V _{GS} = 4.5V, I _D = 2.2A V _{GS} =10V, I _D =2.4A, T _J =125°C	Q1		75 85 100	90 105 140	mΩ
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -4.5V, I _D = -2.5A V _{GS} = -2.5V, I _D = -2.0A V _{GS} = -1.8V, I _D = -1.6A V _{GS} = -4.5V, I _D = 2.5A, T _J = 125°C	Q2		75 97 154 86	90 125 220 120	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 1 mA V _{DS} = -5 V, I _D = -2.5A	Q1 Q2		7 7		S
R _G	Gate Resistance	V _{GS} = 15 mV, f = 1.0 MHz	Q1 Q2		5 13		Ω
Dynamic Characteristics							
C _{iss}	Input Capacitance	For Q1: V _{DS} =15V, V _{GS} =0V, f=1MHz For Q2: V _{DS} =-6V, V _{GS} =0V, f=1MHz	Q1 Q2		270 514		pF
C _{oss}	Output Capacitance		Q1 Q2		50 234		pF
C _{rss}	Reverse Transfer Capacitance		Q1 Q2		20 167		pF
Switching Characteristics (Note 2)							
td(on)	Turn-on Delay Time	For Q1: V _{DS} = 15 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = 6 Ω For Q2: V _{DS} = -10 V, I _D = -1 A, V _{GS} = -4.5 V, R _{GEN} = 6 Ω	Q1 Q2		5 13	10 23	ns
tr	Turn-on Rise Time		Q1 Q2		8 12	16 22	ns
td(off)	Turn-off Delay Time		Q1 Q2		18 22	32 35	ns
tf	Turn-off Fall Time		Q1 Q2		1.2 2.9	2.4 46	ns
Qg	Total Gate Charge		Q1 Q2		2.5 5.7	3.5 8	nC
Qgs	Gate-Source Charge		Q1 Q2		0.7 1.2		nC
Qgd	Gate-Drain Charge	Q1 Q2		0.6 1.7		nC	

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

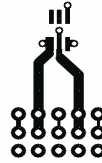
Symbol	Parameter	Test Conditions	Q	Min	Typ	Max	Units
Drain-Source Diode Characteristics							
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.7\text{ A}$, Note 2 $V_{GS} = 0\text{ V}, I_S = -0.8\text{ A}$, Note 2	Q1 Q2		0.6 -0.7	700 1200	mV
t_{RR}	Reverse Recovery Time	For Q1: $I_F = 2.4\text{ A}, dI_F/dt = 300\text{ A}/\mu\text{s}$ For Q2: $I_F = -2.5\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	Q1 Q2		10 24		ns
I_{RM}	Maximum Reverse Recovery Current		Q1 Q2		0.8 -0.5		A
Q_{RR}	Reverse Recovery Charge		Q1 Q2		4 6		nC

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 100°C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 175°C/W when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu\text{s}$, Duty Cycle < 2.0%

Typical Characteristics : Q1

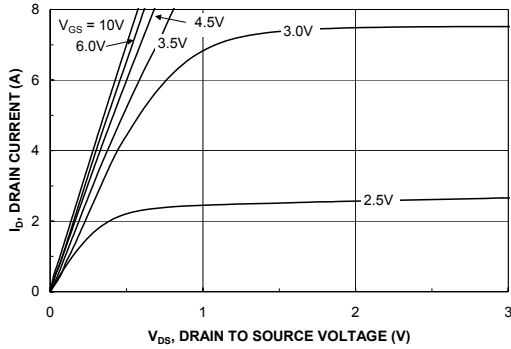


Figure 1. On-Region Characteristics.

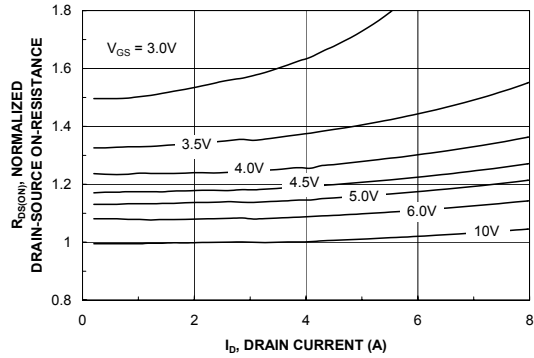


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

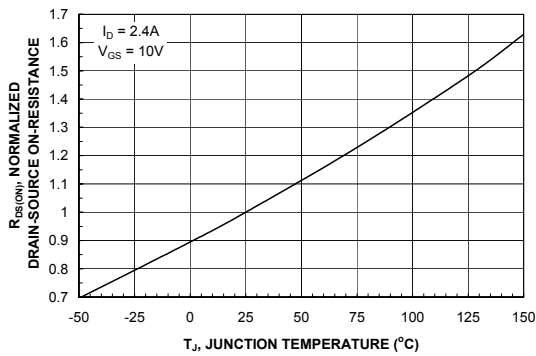


Figure 3. On-Resistance Variation with Temperature.

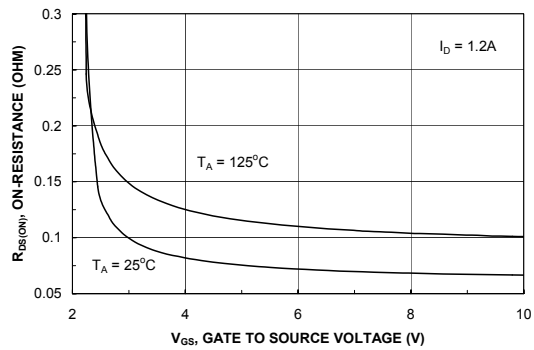


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

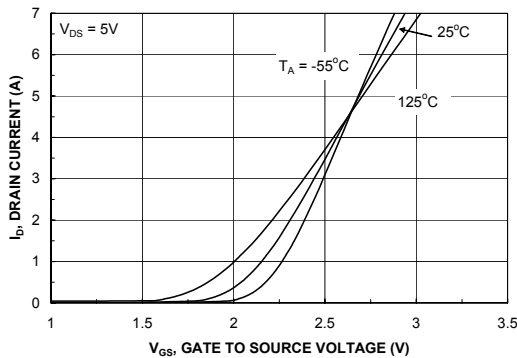


Figure 5. Transfer Characteristics.

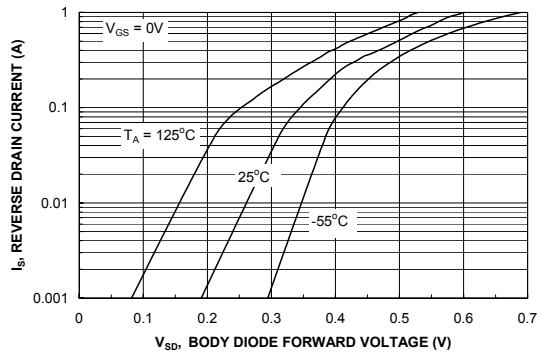


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics : Q1

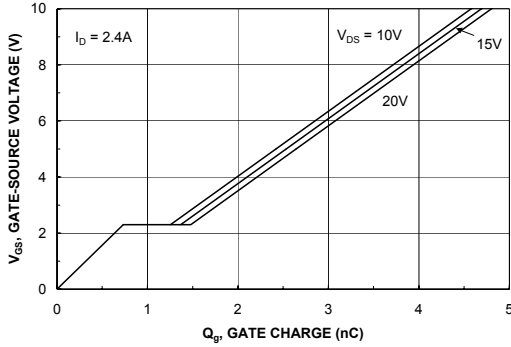


Figure 7. Gate Charge Characteristics.

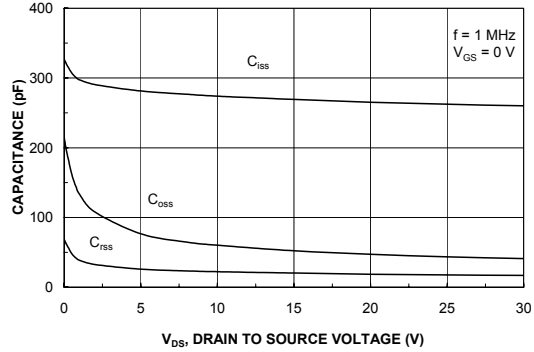


Figure 8. Capacitance Characteristics.

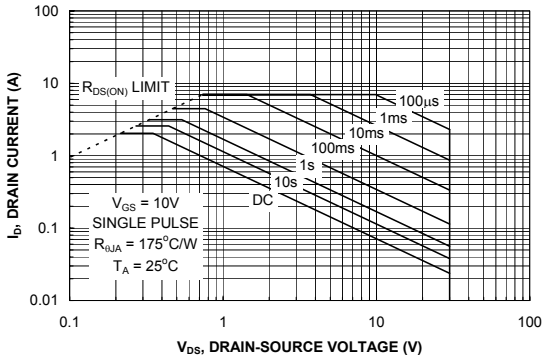


Figure 9. Maximum Safe Operating Area.

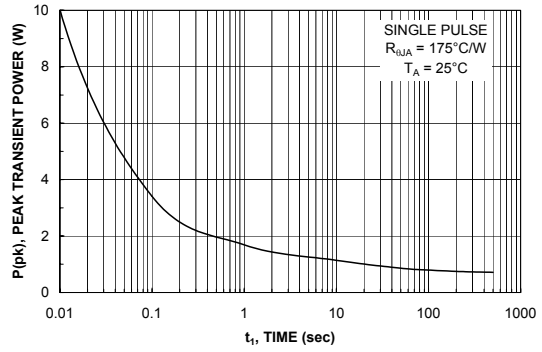


Figure 10. Single Pulse Maximum Power Dissipation.

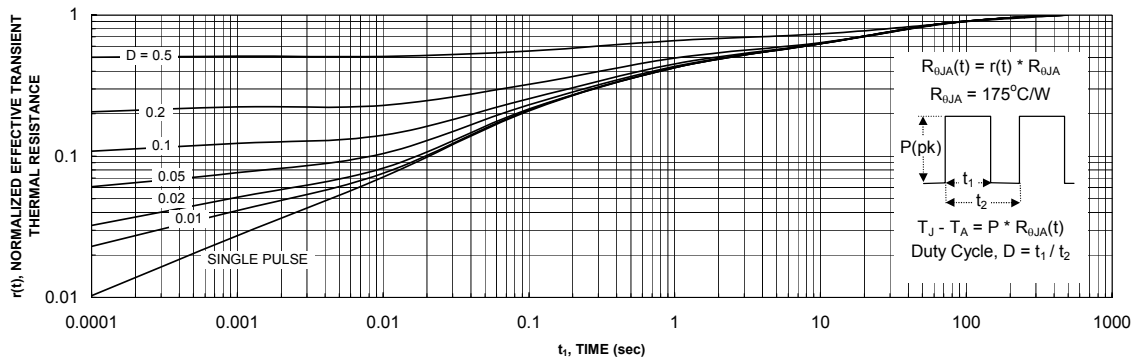


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics : Q2

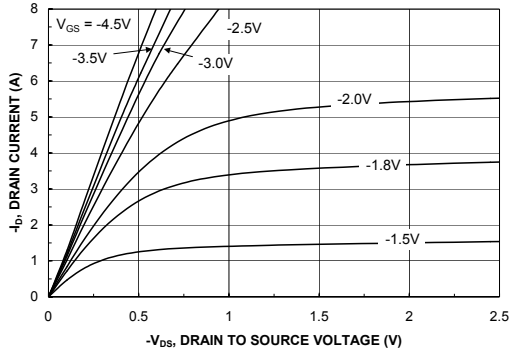


Figure 12. On-Region Characteristics.

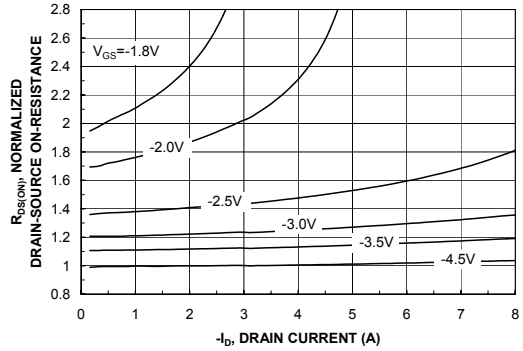


Figure 13. On-Resistance Variation with Drain Current and Gate Voltage.

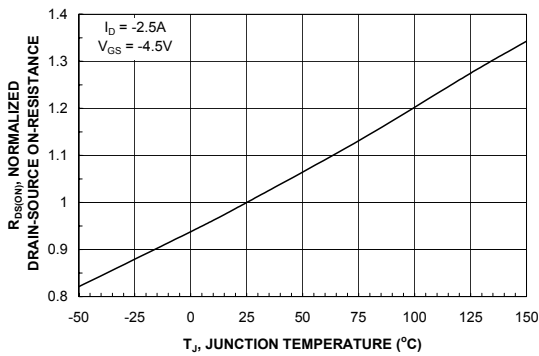


Figure 14. On-Resistance Variation with Temperature.

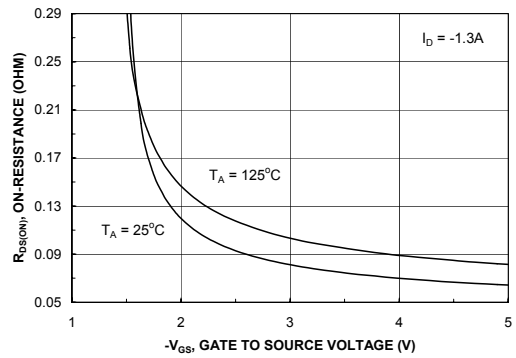


Figure 15. On-Resistance Variation with Gate-to-Source Voltage.

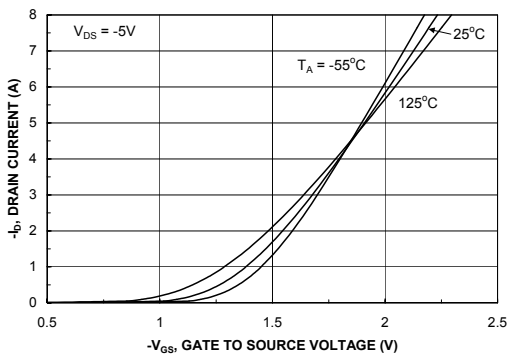


Figure 16. Transfer Characteristics.

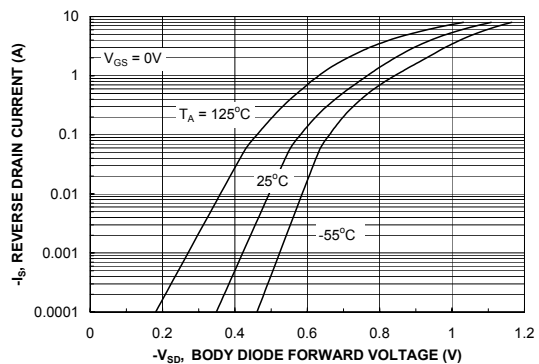


Figure 17. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics : Q2

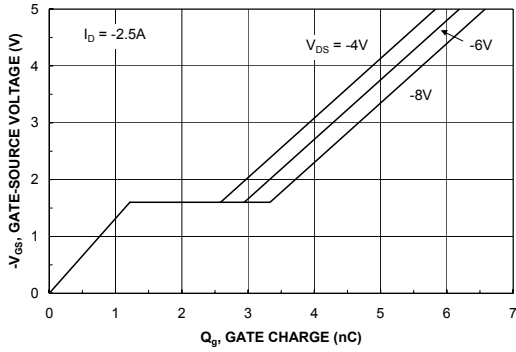


Figure 18. Gate Charge Characteristics.

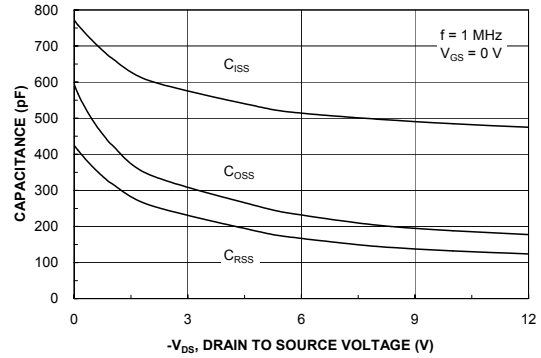


Figure 19. Capacitance Characteristics.

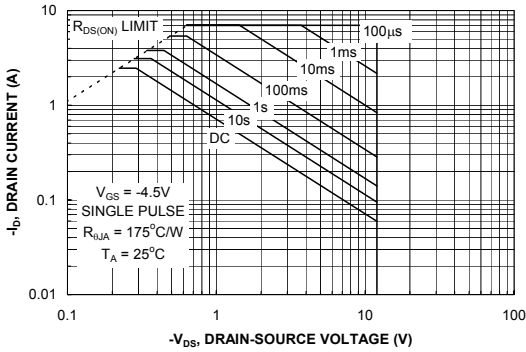


Figure 20. Maximum Safe Operating Area.

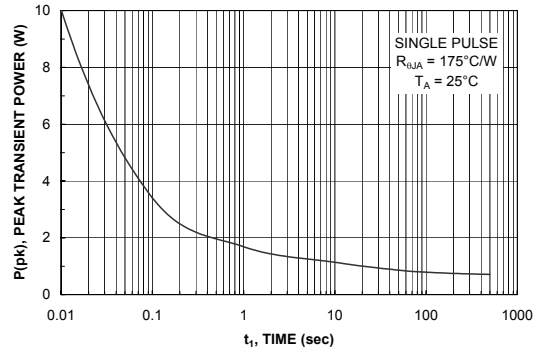


Figure 21. Single Pulse Maximum Power Dissipation.

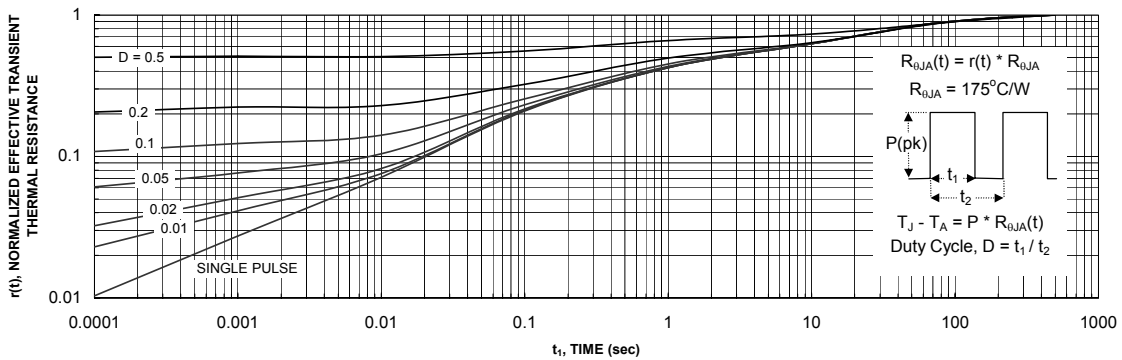


Figure 22. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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